

EFM32TG210 DATASHEET

F32/F16/F8

Preliminary

- ARM Cortex-M3 CPU platform
 - High Performance 32-bit processor @ up to 32 MHz
 - Wake-up Interrupt Controller
- Flexible Energy Management System
 - 20 nA @ 3 V Shutoff Mode
 - 0.6 μA @ 3 V Stop Mode, including Power-on Reset, Brown-out Detector, RAM and CPU retention
 - 1 µA @ 3 V Deep Sleep Mode, including RTC with 32.768 kHz oscillator, Power-on Reset, Brown-out Detector, RAM and CPU retention
 - 51 µA/MHz @ 3 V Sleep Mode
 - 150 µA/MHz @ 3 V Run Mode, with code executed from flash
- 32/16/8 KB Flash
- 4/4/2 KB RAM
- 24 General Purpose I/O pins
 - Configurable Push-pull, Open-drain, pull-up/down, input filter, drive strength
 - Configurable peripheral I/O locations
 - 14 asynchronous external interrupts
 - Output state retention and wakeup from Shutoff Mode
- 8 Channel DMA Controller
- 8 Channel Peripheral Reflex System (PRS) for autonomous inter-peripheral signaling
- Hardware AES with 128/256-bit keys in 54/75 cycles
- Timers/Counters
 - 2x 16-bit Timer/Counter
 - 2x3 Compare/Capture/PWM channels
 - 16-bit Low Energy Timer
 - 24-bit Real-Time Counter
 - 16-bit Pulse Counter
 - Watchdog Timer with dedicated RC oscillator @ 50 nA

Communication interfaces

- 2x Universal Synchronous/Asynchronous Receiver/Transmitter
 - UART/SPI/SmartCard (ISO 7816)/IrDA/I2S
 - Triple buffered full/half-duplex operation
- Low Energy UART
 - Autonomous operation with DMA in Deep Sleep Mode
- I²C Interface with SMBus support
- Address recognition in Stop Mode

• Ultra low power precision analog peripherals

- 12-bit 1 Msamples/s Analog to Digital Converter
 - 4 single ended channels/2 differential channels
 - On-chip temperature sensor
 - Conversion tailgating for predictable latency
- 12-bit 500 ksamples/s Digital to Analog Converter
- 2x Analog Comparator
 - Capacitive sensing with up to 5 inputs
- 3× Operational Amplifier
- 6.1 MHz GBW, Rail-to-rail, Programmable Gain
- Supply Voltage Comparator

• Low Energy Sensor Interface (LESENSE)

- Autonomous sensor monitoring in Deep Sleep Mode
- Wide range supported, including inductive, resistive and capacitive sensors
- Ultra efficient Power-on Reset and Brown-Out Detector
- 2-pin Serial Wire Debug interface
- 1-pin Serial Wire Viewer
- Pre-Programmed Serial Bootloader
- Temperature range -40 to 85 °C
- Single power supply 1.85 to 3.8 V
- QFN32 package

32-bit ARM Cortex-M0, Cortex-M3 and Cortex-M4F microcontrollers for:

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1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32TG210 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (KB)	RAM (KB)	Max Speed (MHz)	Supply Voltage (V)	Temperature	Package
EFM32TG210F8-QFN32	8	2	32	1.85 - 3.8	-40 - 85 °C	QFN32
EFM32TG210F16-QFN32	16	4	32	1.85 - 3.8	-40 - 85 °C	QFN32
EFM32TG210F32-QFN32	32	4	32	1.85 - 3.8	-40 - 85 °C	QFN32

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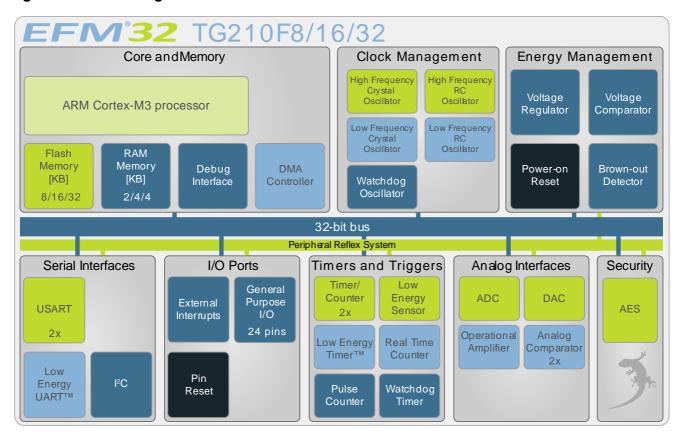
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32TG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also and shows a summary of the configuration for the EFM32TG210 devices. For a complete feature set and indepth information on the modules, the reader is referred to the *EFM32TG Reference Manual*.

A block diagram of the EFM32TG210 is shown in Figure 2.1 (p. 3).

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32 Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface. In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32TG microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is



divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 μ DMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32TG.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32TG microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32TG. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C -bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I^2C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.



2.1.11 Universal Synchronous/Asynchronous Receiver/Transmitter (USART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, I2S devices and IrDA devices.

2.1.12 Pre-Programmed Serial Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Auto-baud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUARTTM, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output.

2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.16 Low Energy Timer (LETIMER)

The unique LETIMERTM, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 – EM3.

2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.



2.1.19 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 4 external pins and 6 internal signals.

2.1.21 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has one single ended output buffer connected to channel 0. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.22 Operational Amplifier (OPAMP)

The EFM32TG210 features 3 Operational Amplifiers. The Operational Amplifier is a versatile general purpose amplifier with rail-to-rail differential input and rail-to-rail single ended output. The input can be set to pin, DAC or OPAMP, whereas the output can be pin, OPAMP or ADC. The current is programmable and the OPAMP has various internal configurations such as unity gain, programmable gain using internal resistors etc.

2.1.23 Low Energy Sensor Interface (LESENSE)

The Low Energy Sensor Interface (LESENSETM), is a highly configurable sensor interface with support for up to 5 individually configurable sensors. By controlling the analog comparators and DAC, LESENSE is capable of supporting a wide range of sensors and measurement schemes, and can for instance measure LC sensors, resistive sensors and capacitive sensors. LESENSE also includes a programmable FSM which enables simple processing of measurement results without CPU intervention. LESENSE is available in energy mode EM2, in addition to EM0 and EM1, making it ideal for sensor monitoring in applications with a strict energy budget.

2.1.24 Advanced Encryption Standard Accelerator (AES)

The AES accelerator performs AES encryption and decryption with 128-bit or 256-bit keys. Encrypting or decrypting one 128-bit data block takes 52 HFCORECLK cycles with 128-bit keys and 75 HFCORECLK cycles with 256-bit keys. The AES module is an AHB slave which enables efficient access to the data and key registers. All write accesses to the AES module must be 32-bit operations, i.e. 8- or 16-bit operations are not supported.

2.1.25 General Purpose Input/Output (GPIO)

In the EFM32TG210, there are 24 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advances configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 16 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.



2.2 Configuration Summary

The features of the EFM32TG210 is a subset of the feature set described in the EFM32TG Reference Manual. Table 2.1 (p. 7) describes device specific implementation of the features.

Table 2.1. Configuration Summary

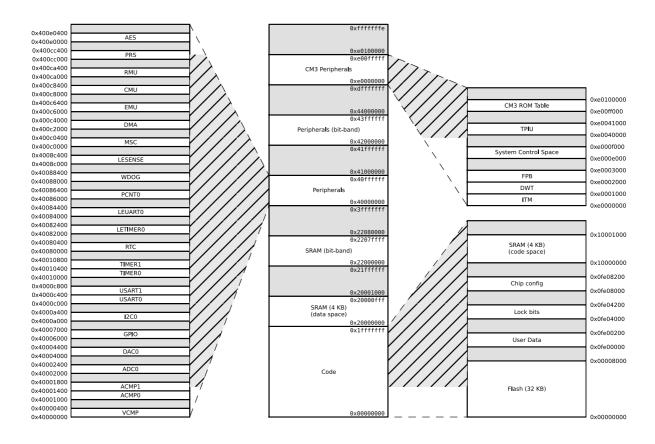
Module	Configuration	Pin Connections
Cortex-M3	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
СМИ	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	12S	US1_TX, US1_RX, US1_CLK, US1_CS
LEUART0	Full configuration	LEU0_TX, LEU0_RX
TIMER0	Full configuration without DTI.	TIM0_CC[2:0]
TIMER1	Full configuration without DTI.	TIM1_CC[2:0]
RTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	16-bit count register	PCNT0_S[1:0]
ACMP0	Full configuration	ACMP0_CH[1:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:5], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:4]
DAC0	Full configuration	DAC0_OUT[0], DAC0_OUTxALT
ОРАМР	Not all pins available	Outputs: OPAMP_OUT0, OPAMP_OUT0ALT, OPAMP_OUT1ALT, OPAMP_OUT2, Inputs: OPAMP_P1, OPAMP_N1, OPAMP_P2
AES	Full configuration	NA
GPIO	24 pins	Available pins are shown in Table 4.3 (p. 49)

2.3 Memory Map

The *EFM32TG210* memory map is shown in Figure 2.2 (p. 8), with RAM and Flash sizes for the largest memory configuration.



Figure 2.2. EFM32TG210 Memory Map with largest RAM and Flash sizes





3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}C$ and $V_{DD}=3.0$ V, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 9), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 9) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 9).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T _{STG}	Storage temperature range		-40		150 ¹	°C
T _S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V _{DDMAX}	External main supply voltage		0		3.8	V
V _{IOPIN}	Voltage on any I/O pin		-0.3		V _{DD} +0.3	V

¹Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Max	Unit
T _{AMB}	Ambient temperature range	-40		85	°C
V _{DDOP}	Operating supply voltage	1.85		3.8	٧
f _{APB}	Internal APB clock frequency			32	MHz
f _{AHB}	Internal AHB clock frequency			32	MHz



3.3.2 Environmental

Table 3.3. Environmental

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ESDHBM}	ESD (Human Body Model HBM)	T _{AMB} =25°C			2	kV
V _{ESDCDM}	ESD (Charged Device Model, CDM)	T _{AMB} =25°C			1	kV

Latch-up sensitivity test passed level A according to JEDEC JESD 78B method Class II, 85°C.



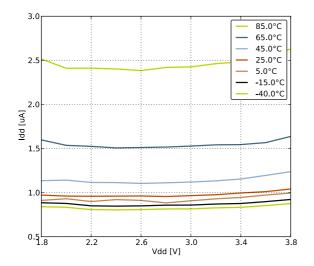
3.4 Current Consumption

Table 3.4. Current Consumption

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		32 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V		157		μΑ/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		150	195	μΑ/ MHz
	EM0 current. No prescal-	21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		153	199	μΑ/ MHz
I _{EM0}	ing. Running prime number calculation code from	14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		155	202	μΑ/ MHz
	Flash.	11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		157	204	μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		162	210	μΑ/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		210		μΑ/ MHz
		32 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V		53		μΑ/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD} = 3.0 V		51	66	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		55	71	μΑ/ MHz
I _{EM1}	EM1 current	14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		56	73	μΑ/ MHz
I _{EM0} ing ber Fla		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		58	75	μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		63	82	μΑ/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V _{DD} = 3.0 V		140		μΑ/ MHz
	EM2 current	EM2 current with RTC at 1 Hz, RTC prescaled to 1kHz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =25°C		1		μΑ
'EM2	LIVIZ CUITETIL	EM2 current with RTC at 1 Hz, RTC prescaled to 1kHz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =85°C		2.4	5	μА
I _{EM} 2	EM3 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.59		μA
-EINI3		V _{DD} = 3.0 V, T _{AMB} =85°C		2	4.5	μΑ
l _{EM4}	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02		μΑ
·CIVI4		V _{DD} = 3.0 V, T _{AMB} =85°C		0.25	0.7	μΑ



Figure 3.1. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



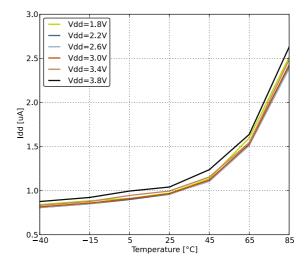
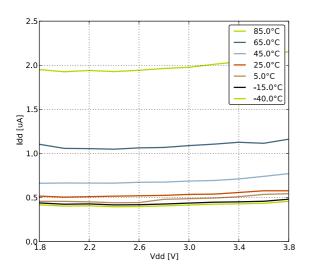


Figure 3.2. EM3 current consumption.



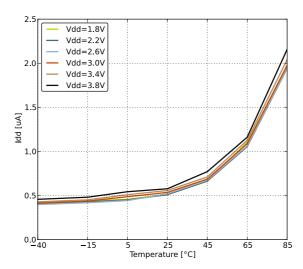
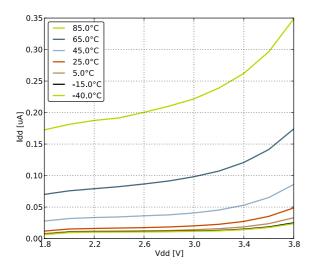
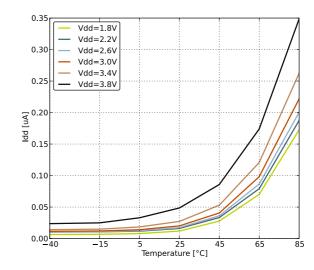


Figure 3.3. EM4 current consumption.







3.5 Transition between Energy Modes

Table 3.5. Energy Modes Transitions

Symbol	Parameter	Min	Тур	Max	Unit
t _{EM10}	Transition time from EM1 to EM0		01		HF core CLK cycles
t _{EM20}	Transition time from EM2 to EM0		2		μs
t _{EM30}	Transition time from EM3 to EM0		2		μs
t _{EM40}	Transition time from EM4 to EM0		163		μs

¹Core wakeup time only.

3.6 Power Management

Table 3.6. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{BODextthr} -	BOD threshold on falling external supply voltage		1.82		1.85	V
V _{BODintthr} -	BOD threshold on falling internally regulated supply voltage		1.62		1.68	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85		V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is re- leased until program execu- tion starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF



3.7 Flash

Table 3.7. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC _{FLASH}	Flash erase cycles before failure		20000			cycles
		T _{AMB} <150°C	10000			h
RET _{FLASH}	Flash data retention	T _{AMB} <85°C	10			years
		T _{AMB} <70°C	20		years µs	
t _{W_PROG}	Word (32-bit) programming time		20			μs
t _{P_ERASE}	Page erase time		20	20.4	20.8	ms
t _{D_ERASE}	Device erase time		40	40.8	41.6	ms
I _{ERASE}	Erase current				7 ¹	mA
I _{WRITE}	Write current				7 ²	mA
V _{FLASH}	Supply voltage during flash erase and write		1.8		3.8	V

¹Measured at 25°C

²Measured at 25°C



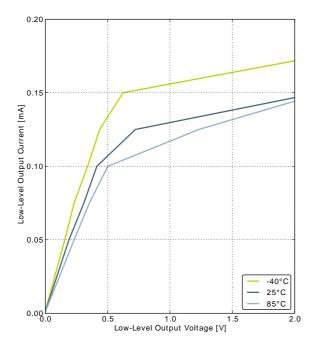
3.8 General Purpose Input Output

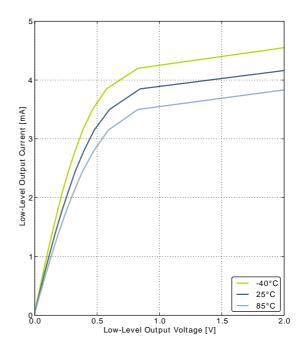
Table 3.8. GPIO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{IOIL}	Input low voltage				0.3V _{DD}	V
V _{IOIH}	Input high voltage		0.7V _{DD}			V
		Sourcing 6 mA, V _{DD} =1.8V, GPIO_Px_CTRL DRIVE- MODE = STANDARD	0.75V _{DD}			V
V	Output high voltage	Sourcing 6 mA, V _{DD} =3.0V, GPIO_Px_CTRL DRIVE- MODE = STANDARD	0.95V _{DD}			V
VIOOH	Output night voltage	Sourcing 20 mA, V _{DD} =1.8V, GPIO_Px_CTRL DRIVE- MODE = HIGH	0.7V _{DD}			V
	VIOIL Input low voltage 0 VIOIH Input high voltage 0 VIOH Input high voltage 0.7 VIOOH Output high voltage Sourcing 6 mA, V _{DD} =1.8V, GPIO, Px_CTRL DRIVE-MODE = STANDARD 0.9 VIOOH Output high voltage Sourcing 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH 0 VIOOL Sourcing 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = STANDARD 0 Sinking 6 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = STANDARD Sinking 6 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = STANDARD Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO, Px_CTRL DRIVE-MODE = HIGH Sinking 20 mA, V _{DD} =3.0V, GPIO,	0.9V _{DD}			V	
		GPIO_Px_CTRL DRIVE-			0.25V _{DD}	V
V _{IOOL}	Output low voltage	GPIO_Px_CTRL DRIVE-			0.05V _{DD}	V
	Output low voltage	GPIO_Px_CTRL DRIVE-			0.3V _{DD}	V
		GPIO_Px_CTRL DRIVE-	0.7V _{DD}	V		
I _{IOLEAK}	Input leakage current				+/-25	nA
R _{PU}	I/O pin pull-up resistor			40		kOhm
R _{PD}	I/O pin pull-down resistor			40		kOhm
R _{IOESD}	Internal ESD series resistor			200		Ohm
^t iogLiTCH	removed by the glitch sup-		10		50	ns
t _{IOOF}	Output fall time	and load capacitance	20+0.1C _L		250	ns
IIOLEAK RPU RPD RIOESD tIOGLITCH tIOOF			20+0.1C _L		250	ns
V _{IOHYST}		V _{DD} = 1.8 - 3.8 V	0.1V _{DD}			V



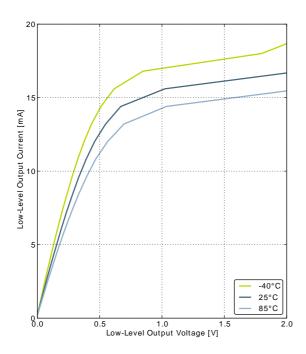
Figure 3.4. Typical Low-Level Output Current, 2V Supply Voltage

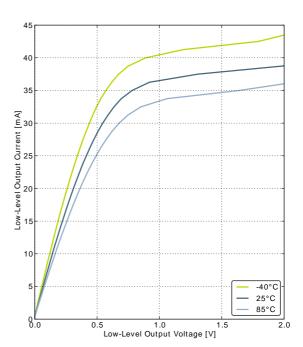




GPIO_Px_CTRL DRIVEMODE = LOWEST





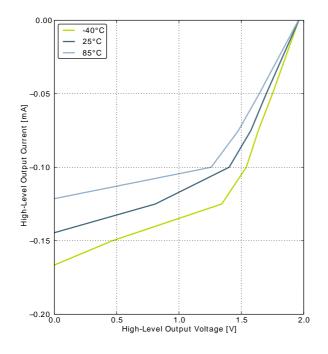


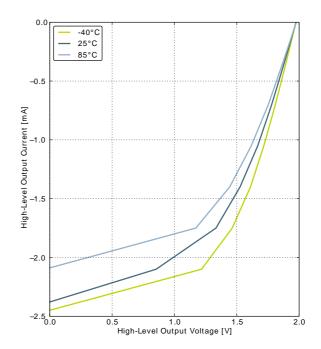
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



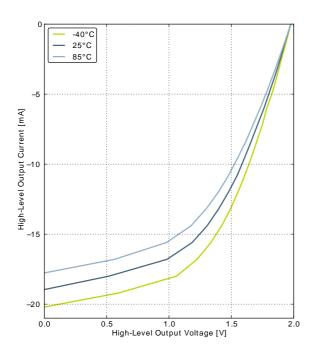
Figure 3.5. Typical High-Level Output Current, 2V Supply Voltage

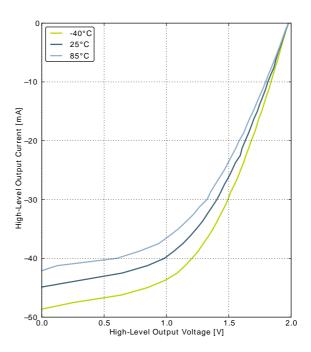




GPIO_Px_CTRL DRIVEMODE = LOWEST





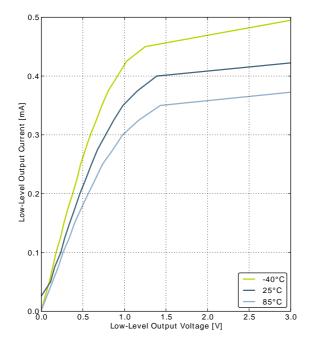


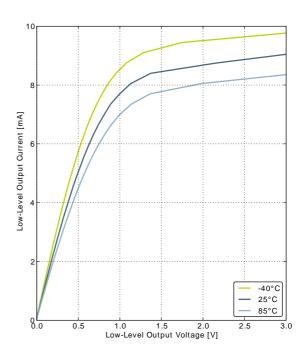
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



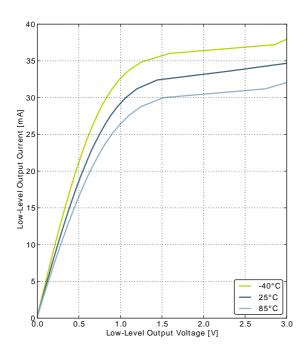
Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage

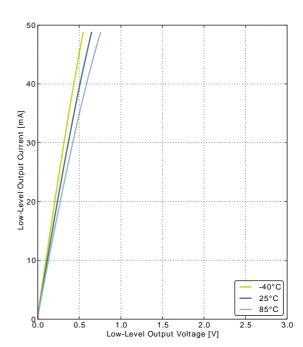




GPIO_Px_CTRL DRIVEMODE = LOWEST





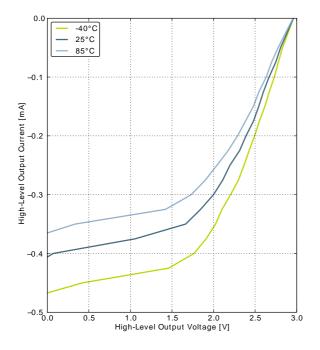


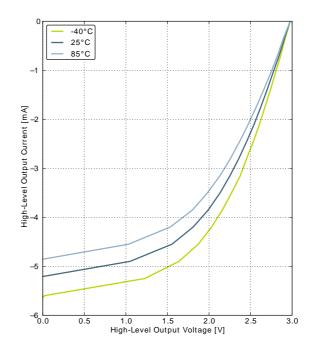
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



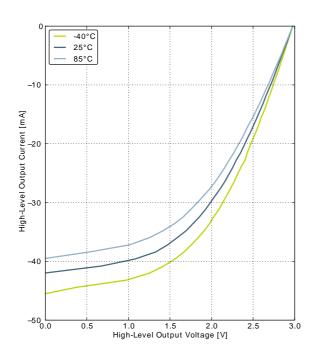
Figure 3.7. Typical High-Level Output Current, 3V Supply Voltage

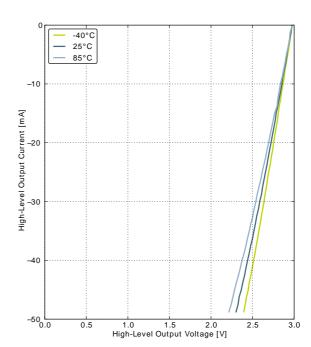




GPIO_Px_CTRL DRIVEMODE = LOWEST





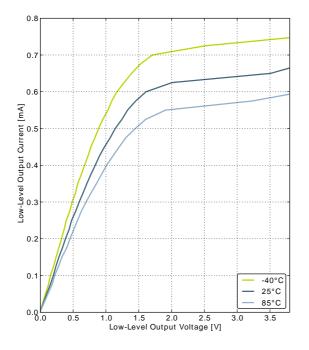


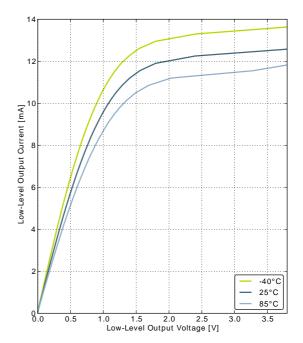
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



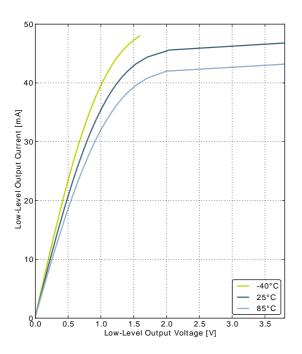
Figure 3.8. Typical Low-Level Output Current, 3.8V Supply Voltage

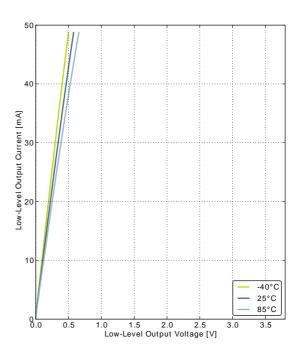




GPIO_Px_CTRL DRIVEMODE = LOWEST





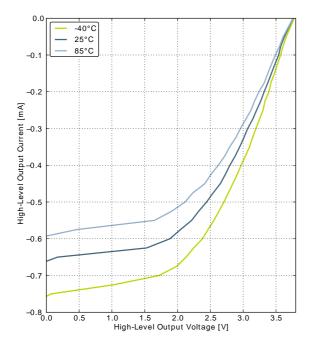


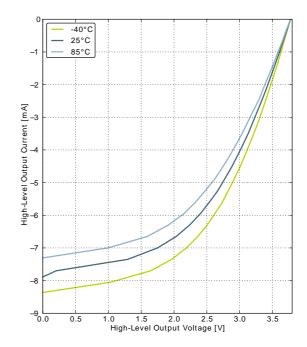
GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



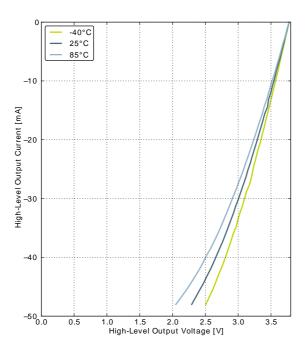
Figure 3.9. Typical High-Level Output Current, 3.8V Supply Voltage

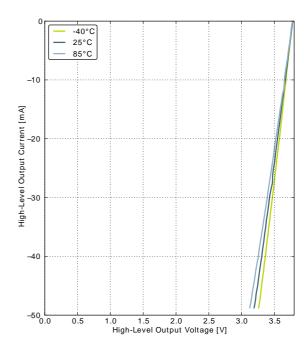




GPIO_Px_CTRL DRIVEMODE = LOWEST







GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH



3.9 Oscillators

3.9.1 LFXO

Table 3.9. LFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR _{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C _{LFXOL}	Supported crystal external load range		5		25	pF
DC _{LFXO}	Duty cycle		48	50	53.5	%
I _{LFXO}	Current consumption for core and buffer after start-up.	ESR=30 kOhm, C _L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t _{LFXO}	Start- up time.	ESR=30 kOhm, C _L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

For safe startup of a given crystal, the load capacitance should be larger than the value indicated in Figure 3.10 (p. 22) and in Table 3.10 (p. 22) for a given LFXOBOOST setting. The minimum supported load capacitance depends on the crystal shunt capacitance, C_0 , which is specified in crystal vendors' datasheet.

Figure 3.10. Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup

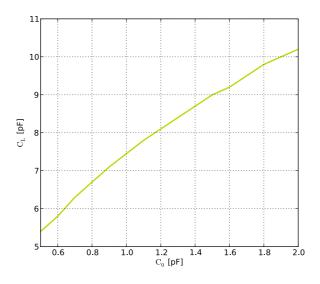


Table 3.10. Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup

Symbol		Capacitance [pF]														
Shunt Capacitance C ₀	0.5	0.6	0.7	0.8	0.9	1.0	1.1	1.2	1.3	1.4	1.5	1.6	1.7	1.8	1.9	2.0
CL _{min} Ifxoboost = 0	5.4	5.8	6.3	6.7	7.1	7.4	7.8	8.1	8.4	8.7	9.0	9.2	9.5	9.8	10.0	10.2



3.9.2 HFXO

Table 3.11. HFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{HFXO}	Supported nominal crystal Frequency		4		32	MHz
ECD	Supported crystal equivalent series resistance	Crystal frequency 32 MHz		30	60	Ohm
ESR _{HFXO}	(ESR)	Crystal frequency 4 MHz		400	1500	Ohm
g _{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C _{HFXOL}	Supported crystal external load range		5		25	pF
DC _{HFXO}	Duty cycle		46	50	54	%
	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C _L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μА
I _{HFXO}		32 MHz: ESR=30 Ohm, C _L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μА
t _{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C _L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μs

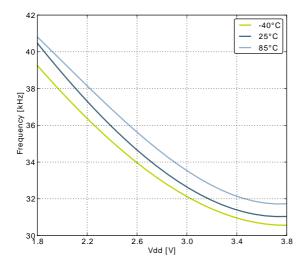
3.9.3 LFRCO

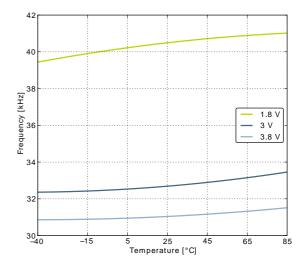
Table 3.12. LFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{LFRCO}	Oscillation frequency , V _{DD} = 3.0 V, T _{AMB} =25°C			32.768		kHz
t _{LFRCO}	Startup time not including software calibration			150		μs
I _{LFRCO}	Current consumption			190		nA
TUNESTEP _L .	Frequency step for LSB change in TUNING value			1.5		%



Figure 3.11. Calibrated LFRCO Frequency vs Temperature and Supply Voltage





3.9.4 HFRCO

Table 3.13. HFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		28 MHz frequency band		28		MHz
· ·		21 MHz frequency band		21		MHz
	Oscillation frequency, V _{DD} =	14 MHz frequency band		14		MHz
fHFRCO	3.0 V, T _{AMB} =25°C 11 MHz frequency band 11		MHz			
		7 MHz frequency band		6.6 ¹		MHz
		1 MHz frequency band		1.2 ²		MHz
t _{HFRCO_settling}	Settling time after start-up	f _{HFRCO} = 14 MHz		0.6		Cycles
		f _{HFRCO} = 28 MHz		106		μA
		f _{HFRCO} = 21 MHz		93		μA
1	Current consumption	f _{HFRCO} = 14 MHz		77		μA
I _{HFRCO}	Current consumption	f _{HFRCO} = 11 MHz		72		μA
		f _{HFRCO} = 6.6 MHz		63		μA
		f _{HFRCO} = 1.2 MHz		22		μA
DC _{HFRCO}	Duty cycle	f _{HFRCO} = 14 MHz	48.5	50	51	%
TUNESTEP _H .	Frequency step for LSB change in TUNING value			0.3		%

¹7 MHz for devices with prod. rev. < 19.

²1 MHz for devices with prod. rev. < 19.



Figure 3.12. Calibrated HFRCO 11 MHz Band Frequency vs Temperature and Supply Voltage

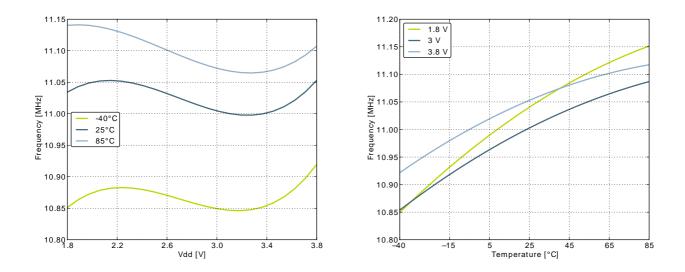


Figure 3.13. Calibrated HFRCO 14 MHz Band Frequency vs Temperature and Supply Voltage

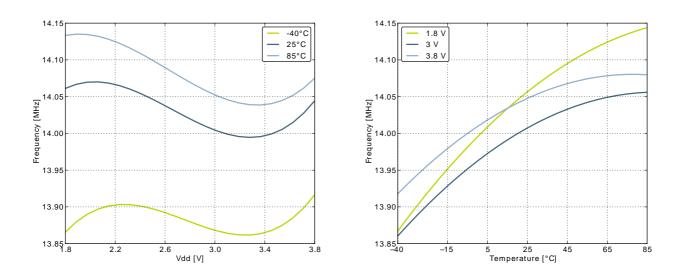
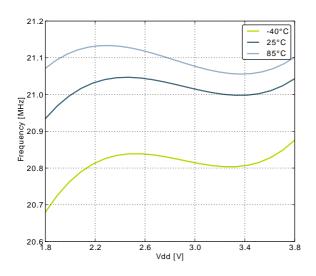


Figure 3.14. Calibrated HFRCO 21 MHz Band Frequency vs Temperature and Supply Voltage



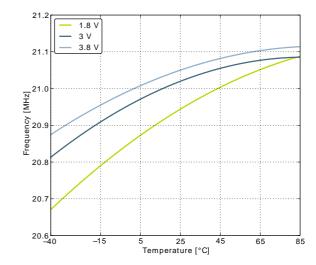
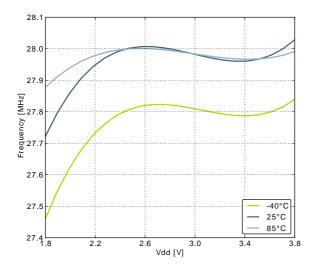
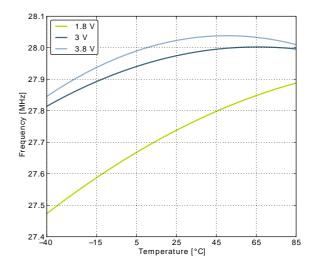




Figure 3.15. Calibrated HFRCO 28 MHz Band Frequency vs Temperature and Supply Voltage





3.9.5 ULFRCO

Table 3.14. ULFRCO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f _{ULFRCO}	Oscillation frequency	25°C, 3V	0.8		1.5	kHz
TC _{ULFRCO}	Temperature coefficient			0.05		%/°C
VC _{ULFRCO}	Supply voltage coefficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.15. ADC

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V	Input voltage range	Single ended	0		V _{REF}	V
V _{ADCIN}		Differential	-V _{REF} /2		V _{REF} /2	V
V _{ADCREFIN}	Input range of external ref- erence voltage, single end- ed and differential		1.25		V _{DD}	V
V _{ADCREFIN_CH7}	Input range of external neg- ative reference voltage on channel 7	See V _{ADCREFIN}	0		V _{DD} - 1.1	V
V _{ADCREFIN_CH6}	Input range of external pos- itive reference voltage on channel 6	See V _{ADCREFIN}	0.625		V _{DD}	V
V _{ADCCMIN}	Common mode input range		0		V _{DD}	V
I _{ADCIN}	Input current	2pF sampling capacitors		<100		nA
CMRR _{ADC}	Analog input common mode rejection ratio			65		dB
	Average active current	1 MSamples/s, 12 bit, external reference		351		μΑ
I _{ADC}	Average active current	10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-		67		μA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		MODE in ADCn_CTRL set to 0b00				
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b01		63		μА
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP- MODE in ADCn_CTRL set to 0b10		64		μА
I _{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μΑ
C _{ADCIN}	Input capacitance			2		pF
R _{ADCIN}	Input ON resistance		1			MOhm
R _{ADCFILT}	Input RC filter resistance			10		kOhm
C _{ADCFILT}	Input RC filter/decoupling capacitance			250		fF
f _{ADCCLK}	ADC Clock Frequency				13	MHz
t _{ADCCONV}	Conversion time	6 bit	7			ADC- CLK Cycles
		10 bit	11			ADC- CLK Cycles
		12 bit	13			ADC- CLK Cycles
t _{ADCACQ}	Acquisition time	Programmable	1		256	ADC- CLK Cycles
t _{ADCACQVDD3}	Required acquisition time for VDD/3 reference		2			μs
	Startup time of reference generator and ADC core in NORMAL mode			5		μs
^t ADCSTART	Startup time of reference generator and ADC core in KEEPADCWARM mode			1		μs
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V refer- ence		63		dB
SNR _{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, V _{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		67		dB
		200 kSamples/s, 12 bit, dif- ferential, internal 1.25V refer- ence		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V _{DD} reference		69		dB
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		70		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V refer- ence		62		dB
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
SNDR _{ADC}	Signal to Noise-puls-Distor-	1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
OTTENADO	tion Ratio (SNDR)	1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V _{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		66		dB
		200 kSamples/s, 12 bit, dif- ferential, internal 1.25V refer- ence		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V _{DD} reference		68		dB
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		69		dB
		1 MSamples/s, 12 bit, single ended, internal 1.25V refer- ence		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V refer- ence		76		dBc
		1 MSamples/s, 12 bit, single ended, V _{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V _{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, 2xV _{DD} reference		75		dBc
SFDR _{ADC}	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V _{DD} reference		76		dBc
		200 kSamples/s, 12 bit, dif- ferential, internal 1.25V refer- ence		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V _{DD} reference		79		dBc

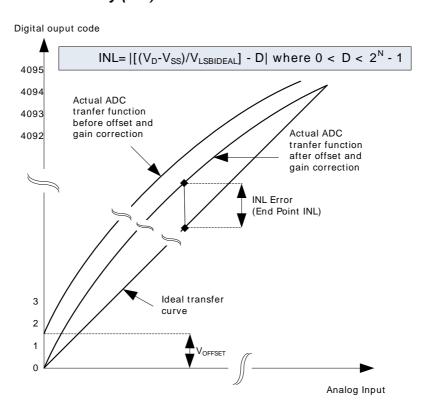


Symbol	Parameter	Condition	Min	Тур	Max	Unit
		200 kSamples/s, 12 bit, differential, 2xV _{DD} reference		79		dBc
V	Offset voltage	After calibration, single ended		0.3		mV
V _{ADCOFFSET}	Oliset voltage	After calibration, differential		0.3		mV
				-1.92		mV/°C
TGRAD _{ADCTH}	Thermometer output gradient			-6.3		ADC Codes/ °C
DNL _{ADC}	Differential non-linearity (DNL)			±0.7		LSB
INL _{ADC}	Integral non-linearity (INL), End point method			±1.2		LSB
MC _{ADC}	No missing codes		11.999 ¹	12		bits
CAINI	Cain arror drift	1.25V reference		0.01 ²	0.033	%/°C
GAIN _{ED}	Gain error drift	2.25V reference		0.01 ²	0.03 ³	%/°C
OFFEET	Offset error drift	1.25V reference		0.22	0.7 ³	LSB/°C
OFFSET _{ED}	Oliset error anit	2.25V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.16 (p. 30) and Figure 3.17 (p. 31), respectively.

Figure 3.16. Integral Non-Linearity (INL)

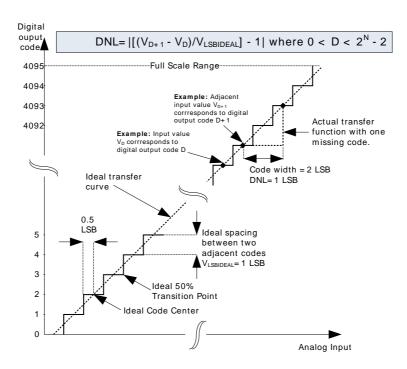


²Typical numbers given by abs(Mean) / (85 - 25).

³Max number given by (abs(Mean) + 3x stddev) / (85 - 25).



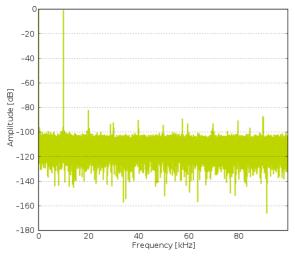
Figure 3.17. Differential Non-Linearity (DNL)



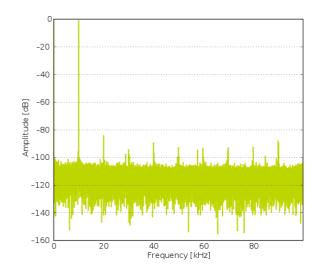


3.10.1 Typical performance

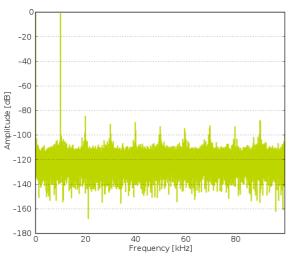
Figure 3.18. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°



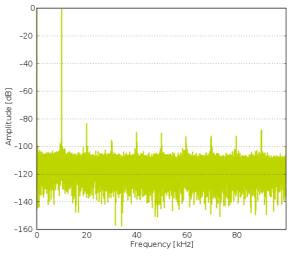




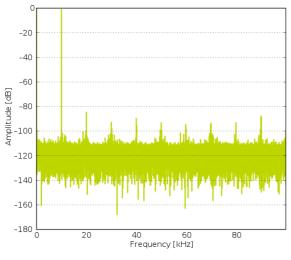
2.5V Reference



2XVDDVSS Reference



5VDIFF Reference



VDD Reference



Figure 3.19. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°

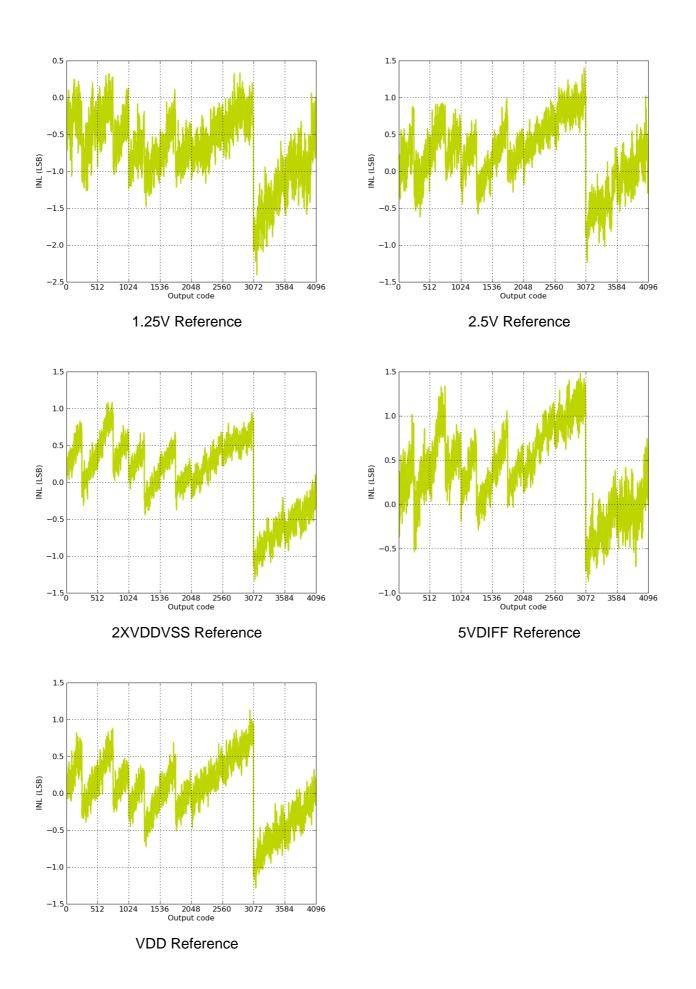




Figure 3.20. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°

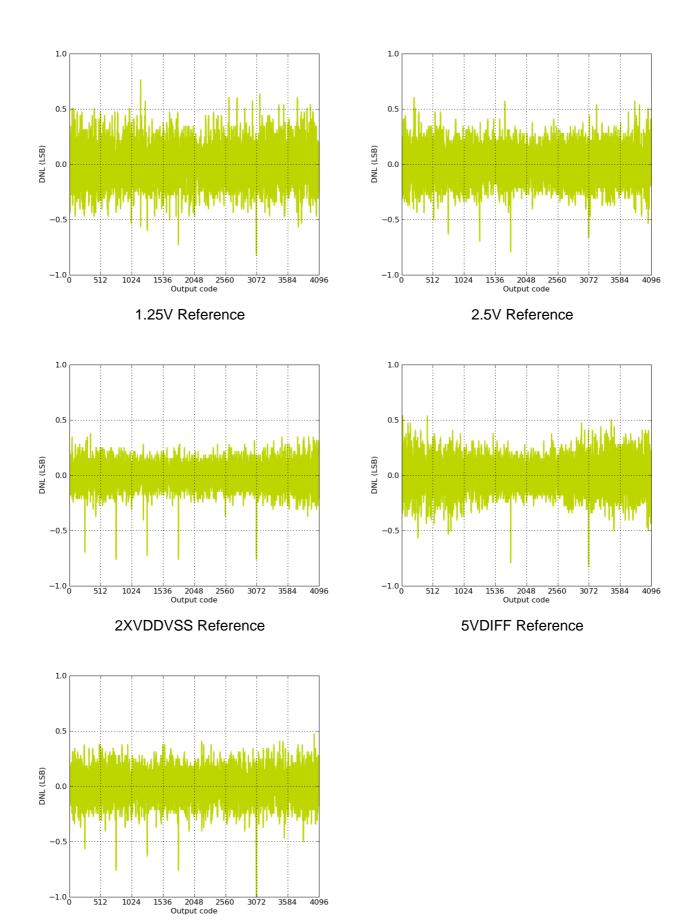




Figure 3.21. ADC Absolute Offset, Common Mode = Vdd /2

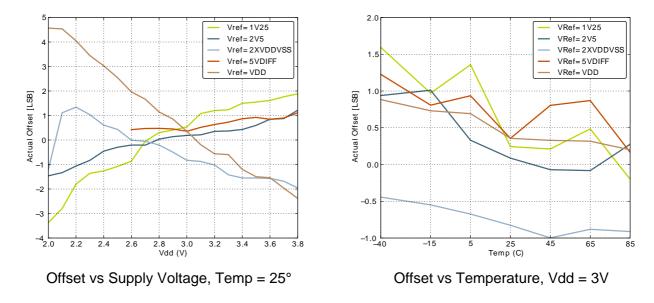
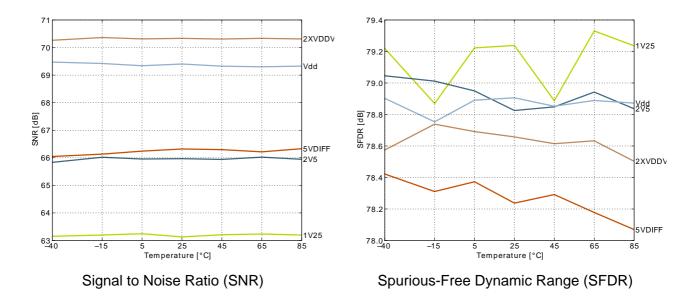


Figure 3.22. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V



3.11 Digital Analog Converter (DAC)

Table 3.16. DAC

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V _{DD}	V
V _{DACCM}	Output common mode voltage range		0		V _{DD}	V
		500 kSamples/s, 12bit		400		μA
I _{DAC}	Active current including ref- erences for 2 channels	100 kSamples/s, 12 bit		200		μA
		1 kSamples/s 12 bit NORMAL		38		μA



Symbol	Parameter	Condition	Min	Тур	Max	Unit
SR _{DAC}	Sample rate				500	ksam- ples/s
		Continuous Mode			1000	kHz
f_{DAC}	DAC clock frequency	Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
CYC _{DACCONV}	Clock cyckles per conversion			2		
t _{DACCONV}	Conversion time		2			μs
t _{DACSETTLE}	Settling time			5		μs
SNID	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
SNR _{DAC}		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
SNDR _{DAC}	Signal to Noise-pulse Dis-	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
SINDINDAC	tortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
CEDD.	Spurious-Free Dynamic	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
SFDR _{DAC}	Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
V _{DACOFFSET}	Offset voltage	After calibration, single ended		2		mV
DNL _{DAC}	Differential non-linearity			±1		LSB
INL _{DAC}	Integral non-linearity			±5		LSB
MC _{DAC}	No missing codes			12		bits

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.17. OPAMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
	Active Current	OPA2 BIASPROG=0xF, HALFBIAS=0x0, Unity Gain		400		μA
I _{OPAMP}		OPA2 BIASPROG=0x7, HALFBIAS=0x1, Unity Gain		100		μΑ
		OPA2 BIASPROG=0x0, HALFBIAS=0x1, Unity Gain		13		μΑ
G _{OL}	Open Loop Gain	OPA2 BIASPROG=0xF, HALFBIAS=0x0		101		dB



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		98		dB
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		91		dB
		OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		16.36		MHz
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		0.81		MHz
GBW _{OPAMP}	Gain Bandwidth Product	OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.11		MHz
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		2.11		MHz
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.72		MHz
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.09		MHz
		BIASPROG=0xF, HALFBIAS=0x0, C _L =75 pF		64		0
PM _{OPAMP}	Phase Margin	BIASPROG=0x7, HALFBIAS=0x1, C _L =75 pF		58		0
		BIASPROG=0x0, HALFBIAS=0x1, C _L =75 pF		58		0
R _{INPUT}	Input Resistance			100		Mohm
D	Load Resistance	OPA0/OPA1	200			Ohm
R_{LOAD}	Load Resistance	OPA2	2000			Ohm
	DO 1 d O	OPA0/OPA1			11	mA
I _{LOAD_DC}	DC Load Current	OPA2			1.5	mA
.,		OPAxHCMDIS=0	V _{SS}		V _{DD}	V
V_{INPUT}	Input Voltage	OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V	Input Offset Voltage	Unity Gain, V _{SS} <v<sub>in<_{DD}, OPAxHCMDIS=0</v<sub>		6		mV
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <v<sub>in<_{DD}-1.2, OPAxHCMDIS=1</v<sub>		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
		OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		46.11		V/µs
SR _{OPAMP}	Slew Rate	OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.21		V/µs
		OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		4.43		V/µs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		1.30		V/µs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.16		V/µs
		OPA0/OPA1 BIASPROG=0xF, HALFBIAS=0x0		0.09		μs
		OPA0/OPA1 BIASPROG=0x7, HALFBIAS=0x1		1.52		μs
PU _{OPAMP}	Power-up Time	OPA0/OPA1 BIASPROG=0x0, HALFBIAS=0x1		12.74		μs
		OPA2 BIASPROG=0xF, HALFBIAS=0x0		0.09		μs
		OPA2 BIASPROG=0x7, HALFBIAS=0x1		0.13		μs
		OPA2 BIASPROG=0x0, HALFBIAS=0x1		0.17		μs
		V _{out} =1V, RESSEL=0, 0.1 Hz <f<10 khz,="" opax-<br="">HCMDIS=0</f<10>		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz <f<10 khz,="" opax-<br="">HCMDIS=1</f<10>		141		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz <f<1 mhz,="" opax-<br="">HCMDIS=0</f<1>		196		μV _{RMS}
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz <f<1 mhz,="" opax-<br="">HCMDIS=1</f<1>		229		μV _{RMS}
		RESSEL=7, 0.1 Hz <f<10 khz,<br="">OPAxHCMDIS=0</f<10>		1230		μV _{RMS}
		RESSEL=7, 0.1 Hz <f<10 khz,<br="">OPAxHCMDIS=1</f<10>		2130		μV _{RMS}
		RESSEL=7, 0.1 Hz <f<1 mhz,<br="">OPAxHCMDIS=0</f<1>		1630		μV _{RMS}
		RESSEL=7, 0.1 Hz <f<1 mhz,<br="">OPAxHCMDIS=1</f<1>		2590		μV _{RMS}

Figure 3.23. OPAMP Common Mode Rejection Ratio

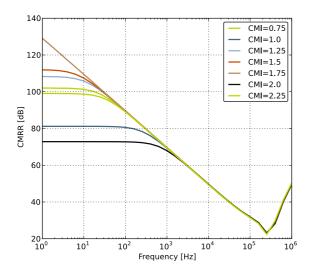


Figure 3.24. OPAMP Positive Power Supply Rejection Ratio

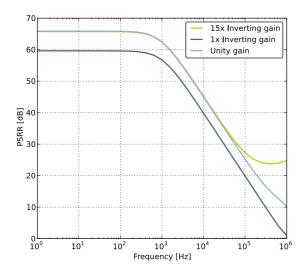


Figure 3.25. OPAMP Negative Power Supply Rejection Ratio

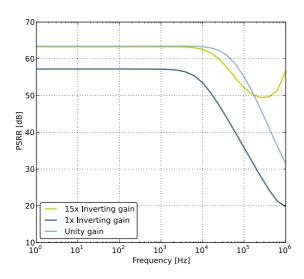




Figure 3.26. OPAMP Voltage Noise Spectral Density (Unity Gain) Vout=1V

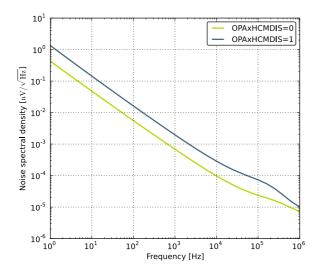
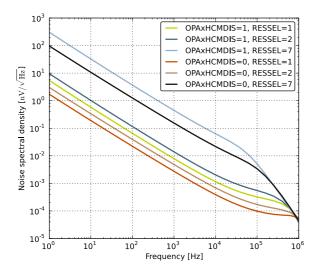


Figure 3.27. OPAMP Voltage Noise Spectral Density (Non-Unity Gain)





3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

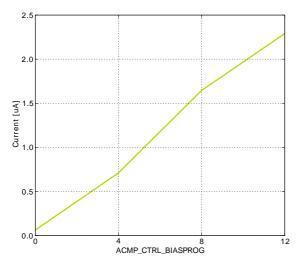
Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{ACMPIN}	Input voltage range		0		V _{DD}	V
V _{ACMPCM}	ACMP Common Mode voltage range		0		V _{DD}	V
		BIASPROG=0b0000, FULL- BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1		μА
I _{ACMP}	Active current	BIASPROG=0b1111, FULL- BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87		μΑ
		BIASPROG=0b1111, FULL- BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195		μА
I _{ACMPREF}	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μΑ
		Internal voltage reference		5		μΑ
V	Offset voltage	Single ended		10		mV
V _{ACMPOFFSET}	Offset voltage	Differential		10		mV
V _{ACMPHYST}	ACMP hysteresis	Programmable		17		mV
		CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
D	Capacitive Sense Internal	CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
R _{CSRES}	Resistance	CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 41) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

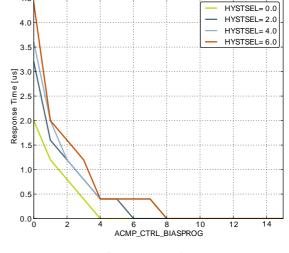
Total ACMP Active Current
$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF}$$
(3.1)



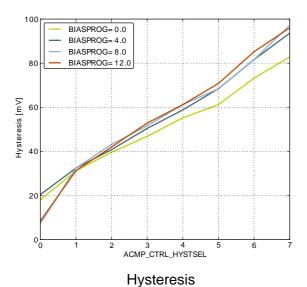
Figure 3.28. Typical ACMP Characteristics













3.14 Voltage Comparator (VCMP)

Table 3.19. VCMP

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V _{VCMPIN}	Input voltage range			V_{DD}		V
V _{VCMPCM}	VCMP Common Mode voltage range			V _{DD}		V
I _{VCMP}		BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.1		μА
	Active current	BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		14.7		μΑ
t _{VCMPREF}	Startup time reference generator	NORMAL		10		μs
V	Offset voltage	Single ended		10		mV
V _{VCMPOFFSET}	Offset voltage	Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			17		mV

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

3.15 Digital Peripherals

Table 3.20. Digital Peripherals

Symbol	Parameter	Condition	Min	Тур	Max	Unit	
I _{USART}	USART current	USART idle current, clock enabled		7.5		μΑ/ MHz	
I _{UART}	UART current	UART idle current, clock enabled		5.63		μΑ/ MHz	
I _{LEUART}	LEUART current	LEUART idle current, clock enabled	· ·				
I _{I2C}	I2C current	I2C idle current, clock enabled		6.25		μΑ/ MHz	
I _{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		8.75		μΑ/ MHz	
I _{LETIMER}	LETIMER current	LETIMER idle current, clock enabled		150		nA	
I _{PCNT}	PCNT current	PCNT idle current, clock enabled		100		nA	
I _{RTC}	RTC current	RTC idle current, clock enabled		100		nA	
I _{AES}	AES current		2.5		μΑ/ MHz		



Symbol	Parameter	Condition	Min	Тур	Max	Unit
I _{GPIO}	GPIO current	GPIO idle current, clock enabled		5.31		μΑ/ MHz
I _{PRS}	PRS current	PRS idle current		2,81		μΑ/ MHz
I _{DMA}	DMA current	Clock enable		8.12		μΑ/ MHz



4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32TG210.

4.1 Pinout

The *EFM32TG210* pinout is shown in Figure 4.1 (p. 45) and Table 4.1 (p. 45). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32TG210 Pinout (top view, not to scale)

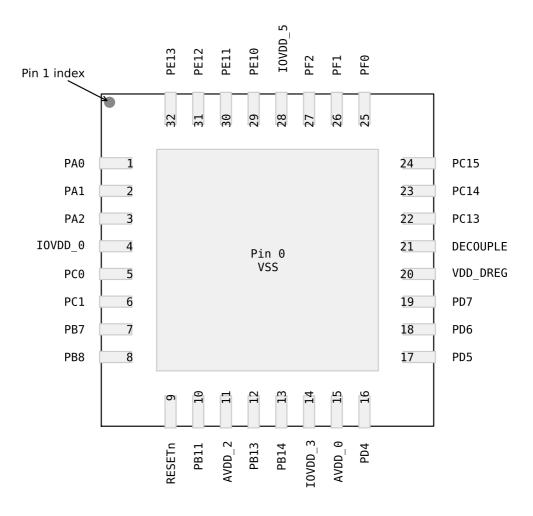


Table 4.1. Device Pinout

	2 Pin# Name	Pin Alternate Functionality / Description					
Pin #	Pin Name	Analog	Timers	Communication	Other		
0	VSS	Ground					
1	PA0		TIM0_CC0 #0/1/4	LEU0_RX #4 I2C0_SDA #0	PRS_CH0 #0 GPIO_EM4WU0		
2	PA1		TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0 PRS_CH1 #0		



	2 Pin# Name		Pin Alternate Functi	onality / Description		
Pin#	Pin Name	Analog	Timers	Communication	Other	
3	PA2		TIM0_CC2 #0/1		CMU_CLK0 #0	
4	IOVDD_0	Digital IO power supply 0.				
5	PC0	DACO_OUTOALT #0/ OPAMP_OUTOALT ACMPO_CH0	TIM0_CC1 #4 PCNT0_S0IN #2	US0_TX #5 US1_TX #0 I2C0_SDA #4	LES_CH0 #0 PRS_CH2 #0	
6	PC1	DAC0_OUT0ALT #1/ OPAMP_OUT0ALT ACMP0_CH1	TIM0_CC2 #4 PCNT0_S1IN #2	US0_RX #5 US1_RX #0 I2C0_SCL #4	LES_CH1 #0 PRS_CH3 #0	
7	PB7	LFXTAL_P	TIM1_CC0 #3	US0_TX #4 US1_CLK #0		
8	PB8	LFXTAL_N	TIM1_CC1 #3	US0_RX #4 US1_CS #0		
9	RESETn	Reset input. Active low, with internal pull-up).			
10	PB11	DAC0_OUT0 #0/ OPAMP_OUT0	TIM1_CC2 #3 LETIM0_OUT0 #1			
11	AVDD_2	Analog power supply 2.				
12	PB13	HFXTAL_P				
13	PB14	HFXTAL_N		US0_CS #4/5 LEU0_RX #1		
14	IOVDD_3	Digital IO power supply 3.				
15	AVDD_0	Analog power supply 0.				
16	PD4	ADC0_CH4 DAC0_P2 #0/ OPAMP_P2		LEU0_TX #0		
17	PD5	ADC0_CH5 DAC0_OUT2 #0/ OPAMP_OUT2		LEU0_RX #0		
18	PD6	ADC0_CH6 DAC0_P1 #0/ OPAMP_P1	TIM1_CC0 #4 LETIM0_OUT0 #0 PCNT0_S0IN #3	US1_RX #2 I2C0_SDA #1	LES_ALTEX0 #0 ACMP0_O #2	
19	PD7	ADC0_CH7 DAC0_N1 #0/ OPAMP_N1	TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2	
20	VDD_DREG	Power supply for on-chip voltage	ge regulator.			
21	DECOUPLE		ltage regulator, nominally at 1.8 e C _{DECOUPLE} is required at this pi			
22	PC13	DAC0_OUT1ALT #1/ OPAMP_OUT1ALT ACMP1_CH5	TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0		LES_CH13 #0	
23	PC14	DAC0_OUT1ALT #2/ OPAMP_OUT1ALT ACMP1_CH6	TIM1_CC1 #0 PCNT0_S1IN #0	US0_CS #3	LES_CH14 #0	
24	PC15	DAC0_OUT1ALT #3/ OPAMP_OUT1ALT ACMP1_CH7	TIM1_CC2 #0	US0_CLK #3	LES_CH15 #0 DBG_SWO #1	
25	PF0		TIM0_CC0 #5 LETIM0_OUT0 #2	US1_CLK #2 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLK #0/1	
26	PF1		TIM0_CC1 #5 LETIM0_OUT1 #2	US1_CS #2 LEU0_RX #3 I2C0_SCL #5	DBG_SWDIO #0/1 GPIO_EM4WU3	
27	PF2		TIM0_CC2 #5	LEU0_TX #4	ACMP1_O #0	



	2 Pin# Name	Pin Alternate Functionality / Description						
Pin #	Pin Name	ne Analog Timers Communication		Communication	Other			
					DBG_SWO #0 GPIO_EM4WU4			
28	IOVDD_5	Digital IO power supply 5.						
29	PE10		TIM1_CC0 #1	US0_TX #0				
30	PE11		TIM1_CC1 #1	US0_RX #0	LES_ALTEX5 #0			
31	PE12		TIM1_CC2 #1	US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 LES_ALTEX6 #0			
32	PE13			US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 #0 ACMP0_O #0 GPIO_EM4WU5			

4.2 Alternate functionality pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 47). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCA-TION bitfield. In these cases, the pinout is shown in the column corresponding to LOCA-TION 0.

Table 4.2. Alternate functionality overview

Alternate			L	OCATIO	N			
Functionality	0	1	2	3	4	5	6	Description
ACMP0_CH0	PC0							Analog comparator ACMP0, channel 0.
ACMP0_CH1	PC1							Analog comparator ACMP0, channel 1.
ACMP0_O	PE13		PD6					Analog comparator ACMP0, digital output.
ACMP1_CH5	PC13							Analog comparator ACMP1, channel 5.
ACMP1_CH6	PC14							Analog comparator ACMP1, channel 6.
ACMP1_CH7	PC15							Analog comparator ACMP1, channel 7.
ACMP1_O	PF2		PD7					Analog comparator ACMP1, digital output.
ADC0_CH4	PD4							Analog to digital converter ADC0, input channel number 4.
ADC0_CH5	PD5							Analog to digital converter ADC0, input channel number 5.
ADC0_CH6	PD6							Analog to digital converter ADC0, input channel number 6.
ADC0_CH7	PD7							Analog to digital converter ADC0, input channel number 7.
CMU_CLK0	PA2		PD7					Clock Management Unit, clock output number 0.
CMU_CLK1	PA1		PE12					Clock Management Unit, clock output number 1.
DAC0_N1 / OPAMP_N1	PD7							Operational Amplifier 1 external negative input.
DAC0_OUT0 / OPAMP_OUT0	PB11							Digital to Analog Converter DAC0_OUT0 / OPAMP output channel number 0.
DAC0_OUT0ALT / OPAMP_OUT0ALT	PC0	PC1						Digital to Analog Converter DAC0_OUT0ALT / OPAMP alternative output for channel 0.
DAC0_OUT1ALT /		PC13	PC14	PC15				Digital to Analog Converter DAC0_OUT1ALT /



Alternate			L	OCATIO	DN			
Functionality	0	1	2	3	4	5	6	Description
OPAMP_OUT1ALT								OPAMP alternative output for channel 1.
DAC0_OUT2 / OPAMP_OUT2	PD5							Digital to Analog Converter DAC0_OUT2 / OPAMP output channel number 2.
DAC0_P1 / OPAMP_P1	PD6							Operational Amplifier 1 external positive input.
DAC0_P2 / OPAMP_P2	PD4							Operational Amplifier 2 external positive input.
								Debug-interface Serial Wire clock input.
DBG_SWCLK	PF0	PF0						Note that this function is enabled to pin out of reset, and has a built-in pull down.
								Debug-interface Serial Wire data input / output.
DBG_SWDIO	PF1	PF1						Note that this function is enabled to pin out of reset, and has a built-in pull up.
								Debug-interface Serial Wire viewer Output.
DBG_SWO	PF2	PC15						Note that this function is not enabled after reset, and must be enabled by software to be used.
GPIO_EM4WU0	PA0							Pin can be used to wake the system up from EM4
GPIO_EM4WU3	PF1							Pin can be used to wake the system up from EM4
GPIO_EM4WU4	PF2							Pin can be used to wake the system up from EM4
GPIO_EM4WU5	PE13							Pin can be used to wake the system up from EM4
HFXTAL_N	PB14							High Frequency Crystal (4 - 32 MHz) negative pin. Also used as external optional clock input pin.
HFXTAL_P	PB13							High Frequency Crystal (4 - 32 MHz) positive pin.
I2C0_SCL	PA1	PD7			PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6			PC0	PF0	PE12	I2C0 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX5	PE11							LESENSE alternate exite output 5.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH13	PC13							LESENSE channel 13.
LES_CH14	PC14							LESENSE channel 14.
LES_CH15	PC15							LESENSE channel 15.
LETIMO_OUTO	PD6	PB11	PF0					Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7		PF1					Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14		PF1	PA0			LEUART0 Receive input.
LEU0_TX	PD4	PB13		PF0	PF2			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8							Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7							Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN	PC13		PC0	PD6				Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	PC14		PC1	PD7				Pulse Counter PCNT0 input number 1.
PRS_CH0	PA0							Peripheral Reflex System PRS, channel 0.



Alternate			L	OCATIO	N			
Functionality	0	1	2	3	4	5	6	Description
PRS_CH1	PA1							Peripheral Reflex System PRS, channel 1.
PRS_CH2	PC0							Peripheral Reflex System PRS, channel 2.
PRS_CH3	PC1							Peripheral Reflex System PRS, channel 3.
TIM0_CC0	PA0	PA0			PA0	PF0		Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	PA1	PA1			PC0	PF1		Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2			PC1	PF2		Timer 0 Capture Compare input / output channel 2.
TIM1_CC0	PC13	PE10		PB7	PD6			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11		PB8	PD7			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12		PB11	PC13			Timer 1 Capture Compare input / output channel 2.
US0_CLK	PE12			PC15	PB13	PB13		USART0 clock input / output.
US0_CS	PE13			PC14	PB14	PB14		USART0 chip select input / output.
								USART0 Asynchronous Receive.
US0_RX	PE11			PE12	PB8	PC1		USART0 Synchronous mode Master Input / Slave Output (MISO).
LICO TV	DE40			DE40	DDZ	DOO		USART0 Asynchronous Transmit.Also used as receive input in half duplex communication.
US0_TX	PE10			PE13	PB7	PC0		USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7		PF0					USART1 clock input / output.
US1_CS	PB8		PF1					USART1 chip select input / output.
								USART1 Asynchronous Receive.
US1_RX	PC1		PD6					USART1 Synchronous mode Master Input / Slave Output (MISO).
US1 TX	PC0		PD7					USART1 Asynchronous Transmit.Also used as receive input in half duplex communication.
031_17	FOU		FUI					USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO pinout overview

The specific GPIO pins available in *EFM32TG210* is shown in Table 4.3 (p. 49). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port in indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

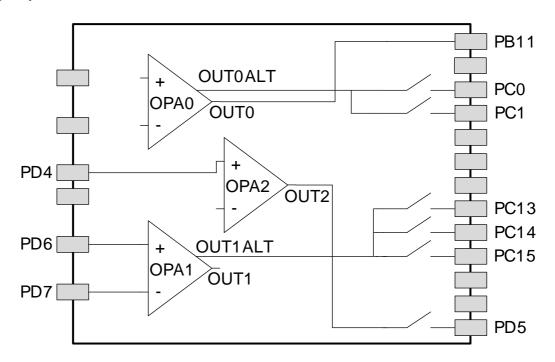
Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	-	-	-	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	PC13	-	-	-	-	-	-	-	-	-	-	-	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	PD4	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	-	-	-	PF2	PF1	PF0

4.4 Opamp pinout overview

The specific opamp terminals available in *EFM32TG210* is shown in Figure 4.2 (p. 50) .

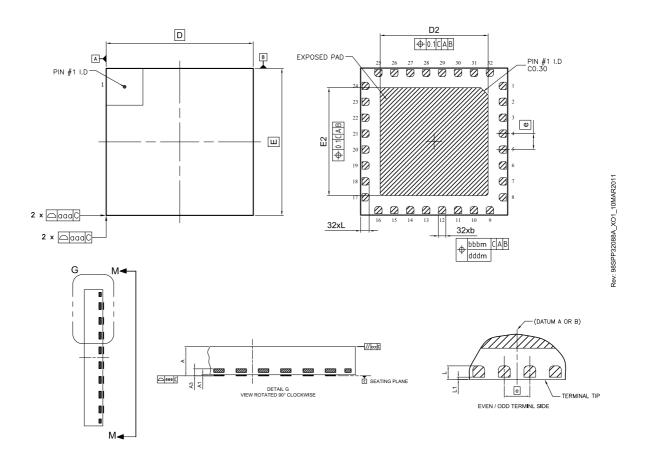


Figure 4.2. Opamp Pinout



4.5 QFN32 Package

Figure 4.3. QFN32



Note:

- 1. Dimensioning & tolerancing confirm to ASME Y14.5M-1994.
- 2. All dimensions are in millimeters. Angles are in degrees.



- 3. Dimension 'b' applies to metallized terminal and is measured between 0.25 mm and 0.30 mm from the terminal tip. Dimension L1 represents terminal full back from package edge up to 0.1 mm is acceptable.
- 4. Coplanarity applies to the exposed heat slug as well as the terminal.
- 5. Radius on terminal is optional

Table 4.4. QFN32 (Preliminary) (Dimensions in mm)

Symbol	A	A1	А3	b	D	E	D2	E2	е	L	L1	aaa	bbb	ССС	ddd	eee
Min	0.80	0.00		0.25			4.30	4.30		0.30	0.00					
Nom	0.85	-	0.203 REF	0.30	6.00 BSC	6.00 BSC	4.40	4.40	0.65 BSC	0.35		0.10	0.10	0.10	0.05	0.08
Max	0.90	0.05		0.35			4.50	4.50		0.40	0.10					

The QFN32 Package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).



5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. QFN32 PCB Land Pattern

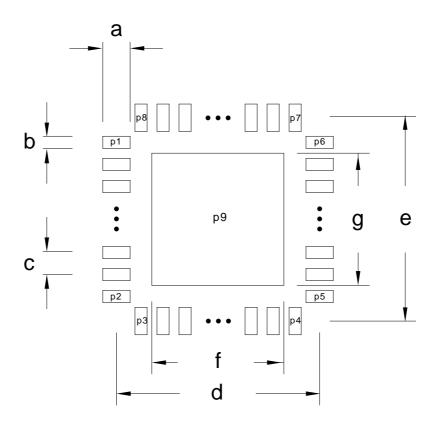


Table 5.1. QFN32 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
а	0.80	P1	1	P6	24
b	0.35	P2	8	P7	25
С	0.65	P3	26	P8	32
d	6.00	P4	16	P9	33
е	6.00	P5	17	-	-
f	4.40	-	-	-	-
g	4.40	-	-	-	-



Figure 5.2. QFN32 PCB Solder Mask

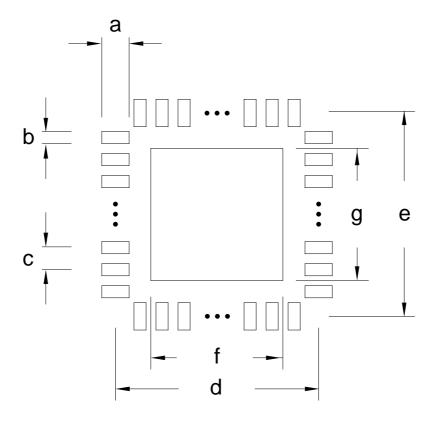


Table 5.2. QFN32 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
а	0.92
b	0.47
С	0.65
d	6.00
е	6.00
f	4.52
g	4.52



Figure 5.3. QFN32 PCB Stencil Design

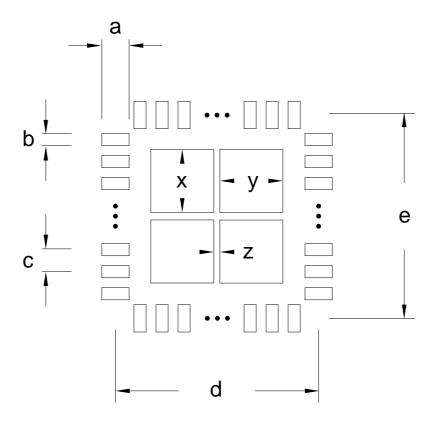


Table 5.3. QFN32 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
а	0.70
b	0.25
С	0.65
d	6.00
е	6.00
х	1.30
У	1.30
z	0.50

- 1. The drawings are not to scale.
- 2. All dimensions are in millimeters.
- 3. All drawings are subject to change without notice.
- 4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
- 5. Stencil thickness 0.125 mm.

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions.

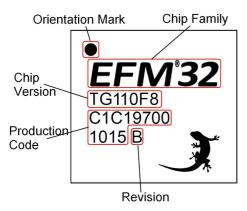


6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 55). If the revision says "ES" (Engineering Sample), the revision must be read out electronically as specified in the reference manual.

6.3 Errata

Please see the dxxxx_efm32tg210_errata.pdf for description and resolution of device erratas. This document is available in Simplicity Studio or online at http://www.energymicro.com/downloads/datasheets.



7 Revision History

7.1 Revision 1.00

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Added GPIO_EM4WU3, GPIO_EM4WU4 and GPIO_EM4WU5 pins and removed GPIO_EM4WU1 in the Alternate functionality overview table.

Other minor corrections.

7.2 Revision 0.96

May 4th, 2012

Corrected PCB footprint figures and tables.

7.3 Revision 0.95

February 27th, 2012

Corrected operating voltage from 1.8 V to 1.85 V.

Added rising POR level and corrected Thermometer output gradient in Electrical Characteristics section.

Updated Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup.

Added Gain error drift and Offset error drift to ADC table.

Added reference to errata document.

7.4 Revision 0.92

July 22nd, 2011

Updated current consumption numbers from latest device characterization data

Updated OPAMP electrical characteristics

Made ADC plots render properly in Adobe Reader

7.5 Revision 0.91

February 4th, 2011

Corrected max DAC sampling rate.

Increased max storage temperature.

Added data for <150°C and <70°C on Flash data retention.

Changed latch-up sensitivity test description.

Added IO leakage current



Added Flash current consumption

Updated HFRCO data

Updated LFRCO data

Added graph for ADC Absolute Offset over temperature

Added graph for ADC Temperature sensor readout

Updated OPAMP electrical characteristics

7.6 Revision 0.90

December 1st, 2010

New peripherals added to pinout, including LESENSE and OpAmps.

7.7 Revision 0.50

May 25th, 2010

Block diagram update.

7.8 Revision 0.40

March 26th, 2010

Initial preliminary release.



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